

SANYO	No.3810	2SJ225
	P-Channel MOS Silicon FET	
Very High-Speed Switching Applications		

Features

- Small ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Meets radial taping.

Absolute Maximum Ratings at Ta = 25°C

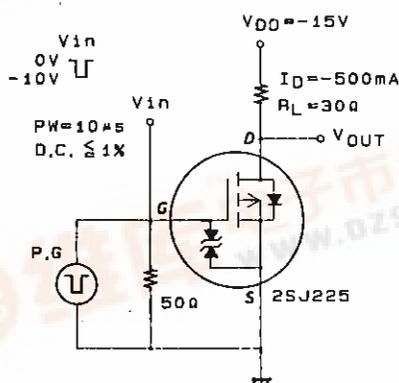
			unit
Drain to Source Voltage	V _{DSS}	-30	V
Gate to Source Voltage	V _{GSS}	±15	V
Drain Current (DC)	I _D	-1	A
Drain Current (Pulse)	I _{DP}	-4	A
Allowable Power Dissipation	P _D	1	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

PW ≤ 10μs, duty cycle ≤ 1%

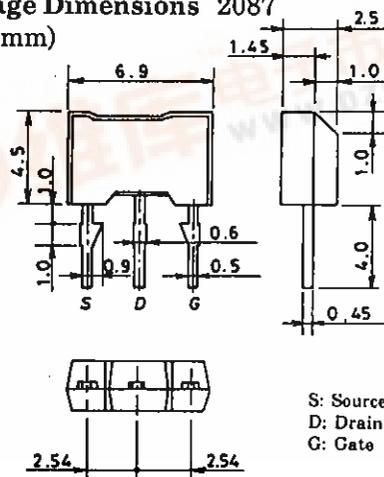
Electrical Characteristics at Ta = 25°C

		min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	-30			V
Zero Gate Voltage Drain Current	I _{DSS}			-100	μA
Gate to Source Leakage Current	I _{GSS}			±10	μA
Cutoff Voltage	V _{GS(off)}	-1.0		-2.0	V
Forward Transfer Admittance	Y _{fs}	0.6	1.0		S
Static Drain to Source on State Resistance	R _{DSON}		0.5	0.75	Ω
	R _{DSON}		0.75	1.1	Ω
Input Capacitance	C _{iss}		170		pF
Output Capacitance	C _{oss}		110		pF
Reverse Transfer Capacitance	C _{rss}		20		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.			ns
Rise Time	t _r	"			ns
Turn-OFF Delay Time	t _{d(off)}	"			ns
Fall Time	t _f	"			ns
Diode Forward Voltage	V _{SD}		-0.9		V

Switching Time Test Circuit

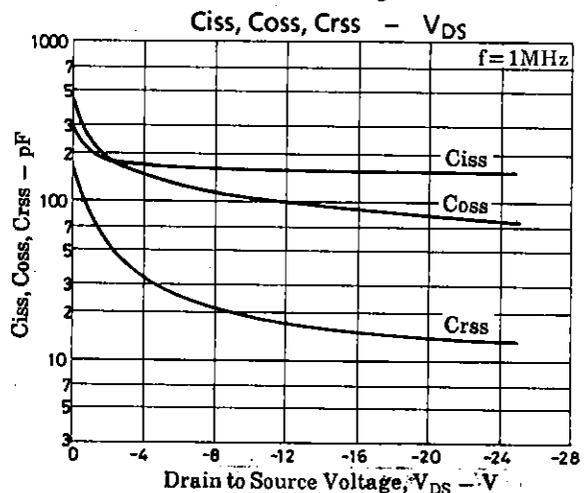
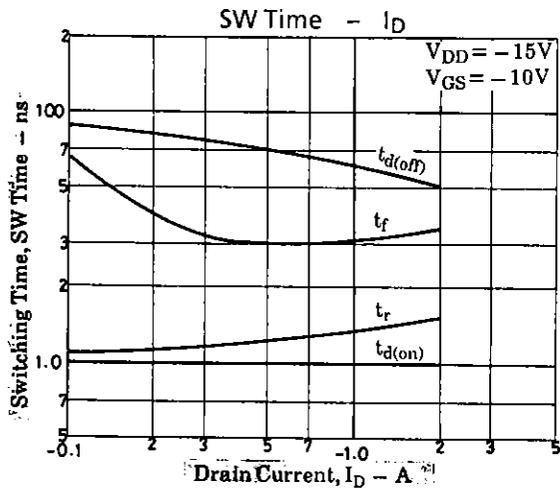
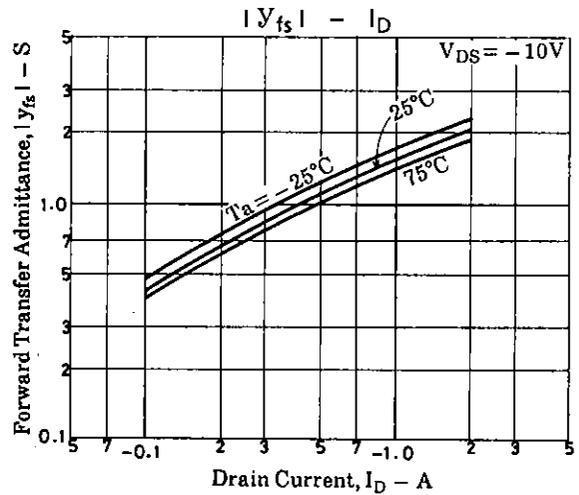
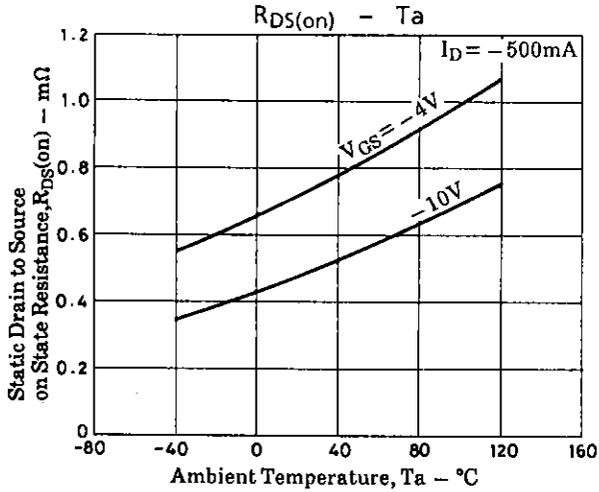
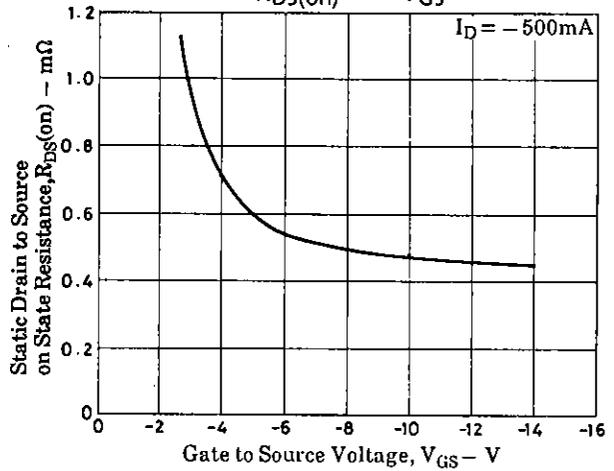
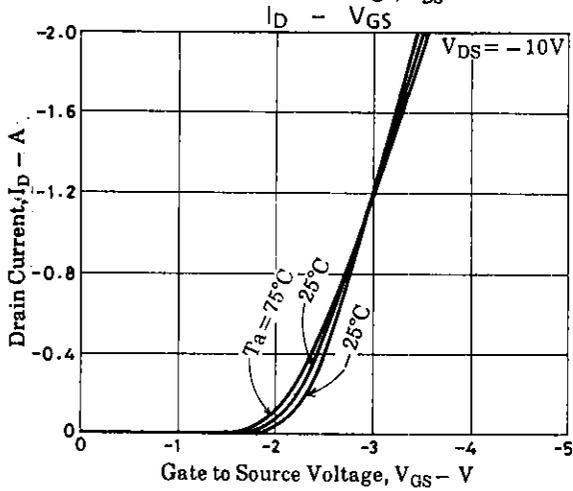
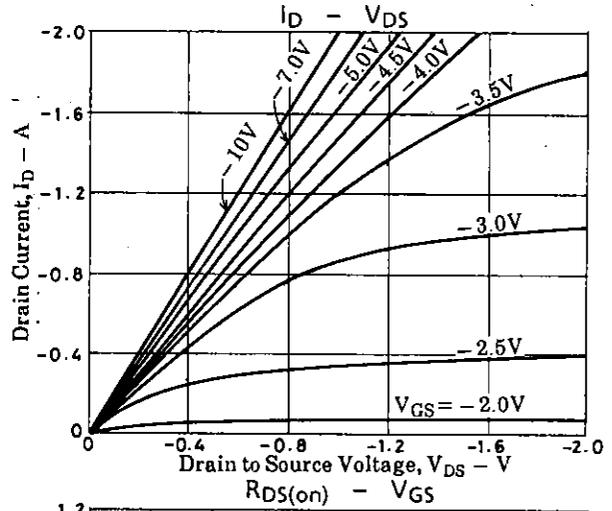
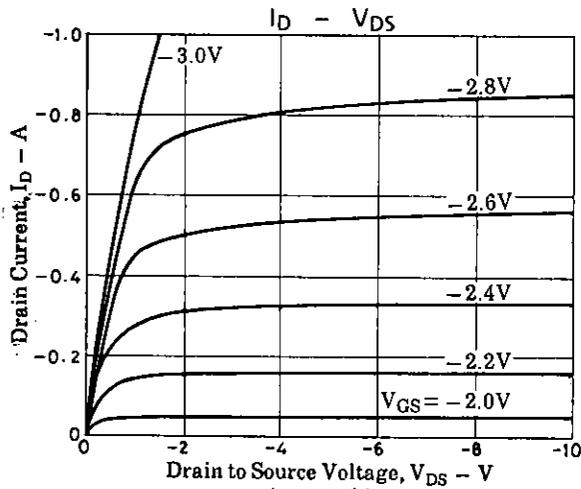


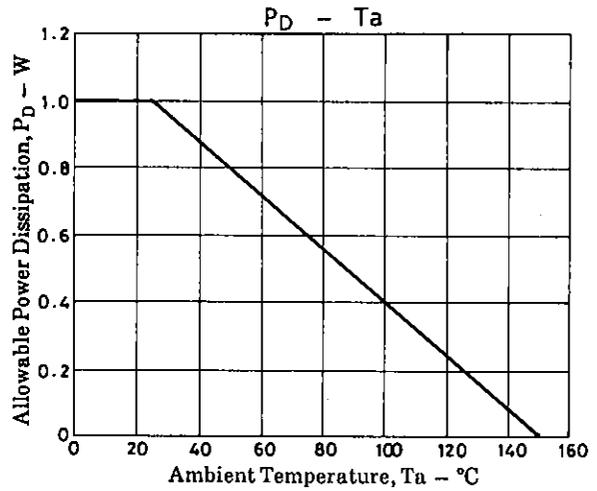
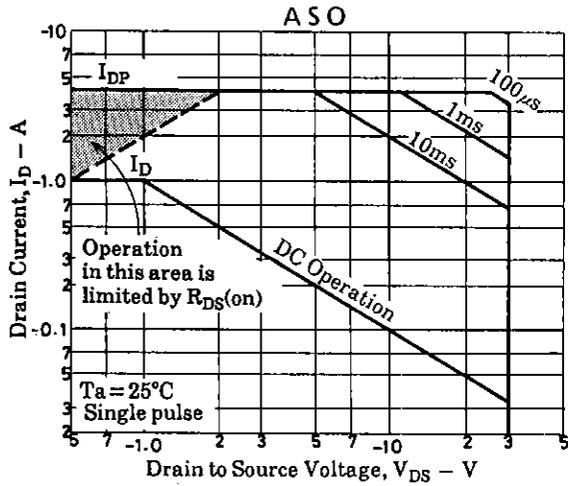
Package Dimensions 2087
(unit: mm)



S: Source
D: Drain
G: Gate
SANYO: NMP







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